



# YJB115G15H

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## N-Channel Enhancement Mode Field Effect Transistor

### Product Summary

$V_{DS}$	150V
$I_D$	115A
$R_{DS(ON)}$	







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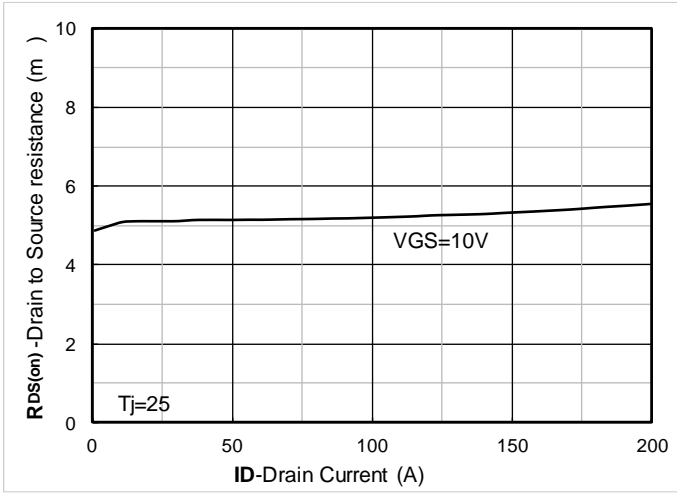


Figure 7. RDS(on) VS Drain Current

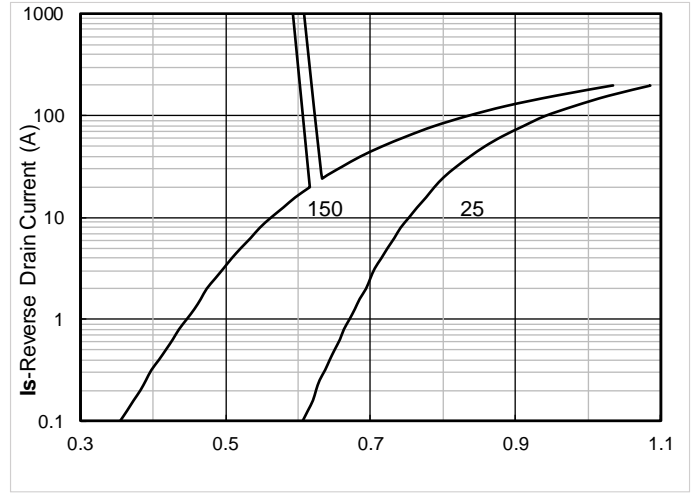


Figure 8. Forward characteristics of reverse diode

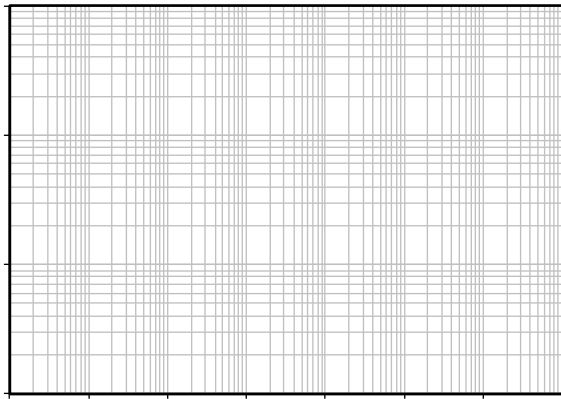


Figure 13. Maximum Transient Thermal Impedance

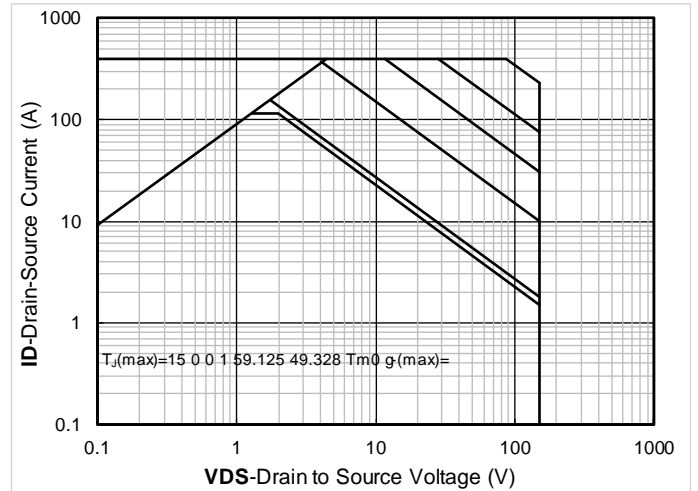


Figure 14. Safe Operation Area

## Test Circuits & Waveforms

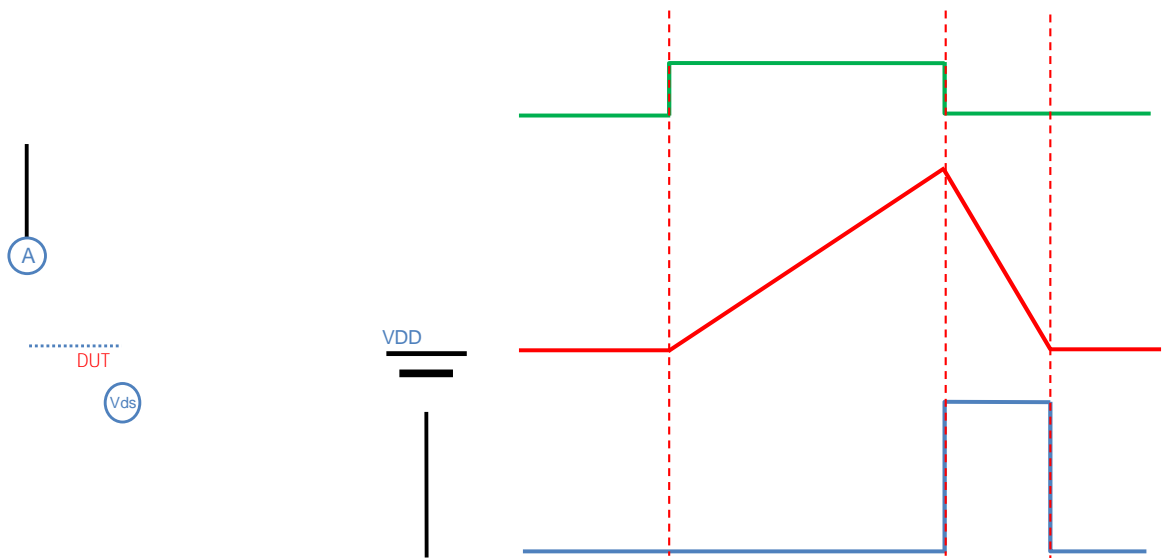


Figure A. Unclamped Inductive Switching (UIS) Test Circuit & Waveform

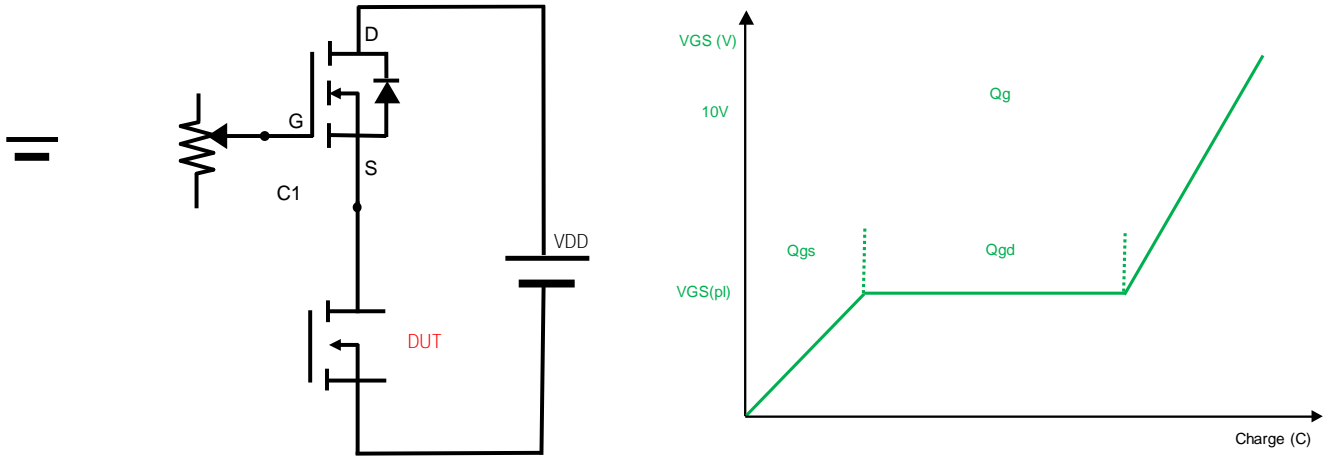


Figure B. Gate Charge Test Circuit & Waveform

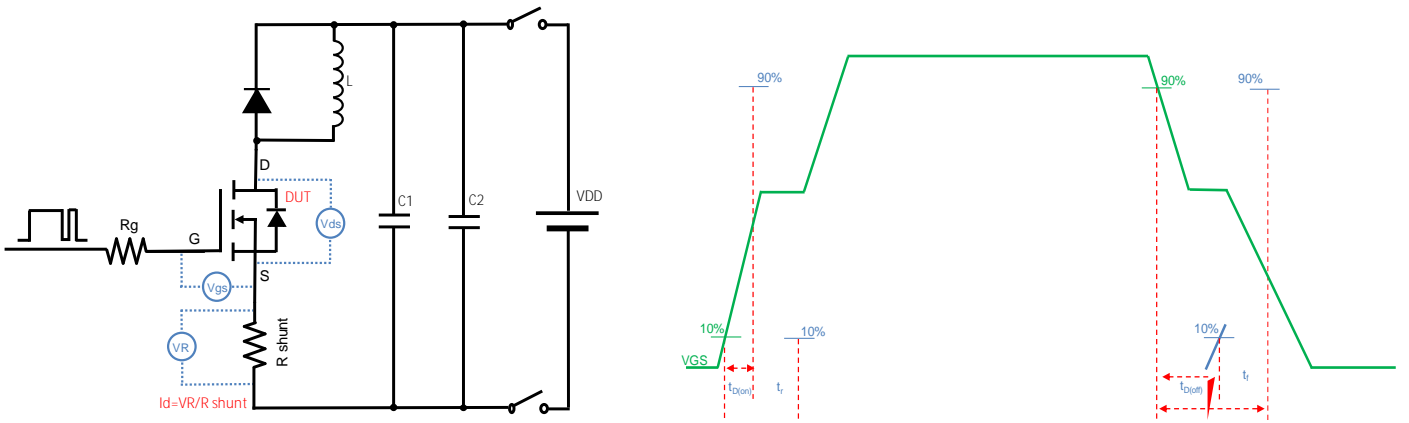


Figure C. Resistive Switching Test Circuit & Waveform

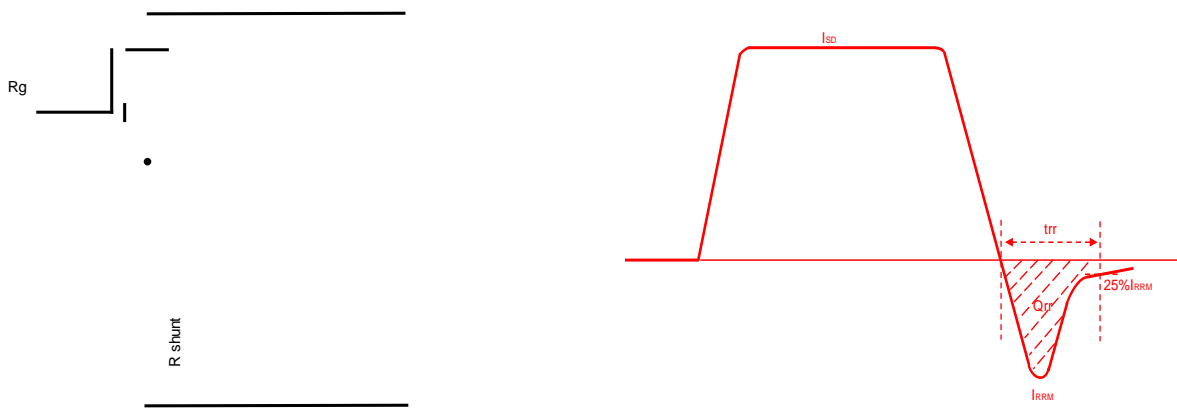


Figure D. Diode Recovery Test Circuit & Waveform



## TO-263-HY Package information

SYM.	MIN.
A2	
b2	0.050
c	
c2	
D2	
E	
E1	



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## Disclaimer

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The product listed herein is designed to be used with ordinary electronic equipment or devices, and not designed to be used with